AMENDMENTS TO THE SPECIFICATION

On Page 4, lines 3 – 13 please make changes, as shown.

The device 100 includes a substrate 101, such as monocrystalline silicon. As the device 100 is an SOI device, a buried oxide layer is disposed over the substrate 101 and is formed by standard fabrication methods. A bulk Si layer 103 is disposed over the SOI layer 102, and is the n^--type drift region of the illustrative device 100. A field oxide 104 is disposed over the n^--drift layer 103. A p^+ type body 105 has a p+ body contact 106 is formed in contact with the p^- body 105. Adjacent to the p+ body contact 106 is the n+ source 107, which has a source metallization 110 as shown. An n+ drain 108 is disposed as shown and has a drain metallization 112 thereover. A field plate 109 is segmented as referenced above, having segments 114 and is illustratively metal, and a gate doped polysilicon (poly) field plate 111 is similarly segmented, having segments 115. Finally, a dielectric layer 113, such as silicon nitride ~~is disposed beneath the poly field plate 111.~~ is disposed beneath the field plate 109. Under the polysilicon field plate 111, there is an oxide layer 117 (as indicated by arrowed vertical lines). In an example process, the thickness of the oxide is about 600 Å.